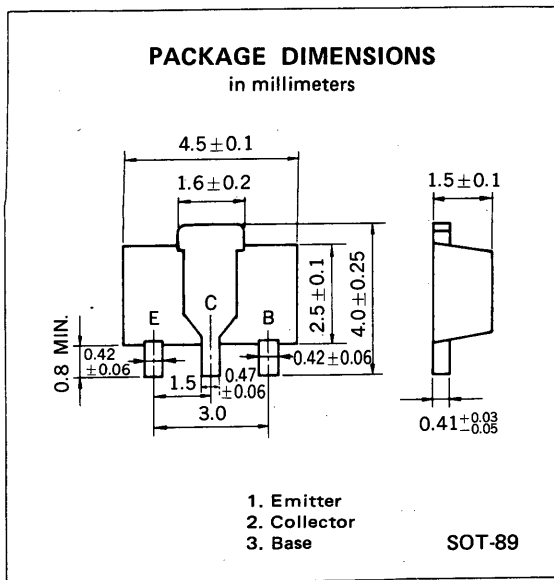


SILICON TRANSISTORS
2SD1006, 2SD1007

NPN SILICON EPITAXIAL TRANSISTOR
POWER MINI MOLD

DESCRIPTION

The 2SD1006 and 2SD1007 are designed for audio frequency power amplifier application, especially in Hybrid Integrated Circuits.



FEATURES

- World Standard Miniature Package : SOT-89
- High Collector to Emitter Voltage : $V_{CE0} > 120$ V (2SD1007)
: $V_{CE0} > 100$ V (2SD1006)
- Complement to PNP type 2SB805 and 2SB806 respectively.

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents ($T_a = 25^\circ\text{C}$)	2SD1006	2SD1007	
Collector to Base Voltage	V_{CBO} 100	120	V
Collector to Emitter Voltage	V_{CEO} 100	120	V
Emitter to Base Voltage	V_{EBO} 5.0		V
Collector Current (DC)	I_C 0.7		A
Collector Current (Pulse)*	I_C 1.2		A
Maximum Power Dissipation			
Total Power Dissipation at 25°C Ambient Temperature**	P_T 2.0		W
Maximum Temperatures			
Junction Temperature	T_j 150		$^\circ\text{C}$
Storage Temperature Range	T_{stg} -55 to +150		$^\circ\text{C}$

*PW \leq 10 ms, duty cycle \leq 50 %

**When mounted on ceramic substrate of $16\text{ cm}^2 \times 0.7\text{ mm}$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
						2SD1006	2SD1007
Collector Cutoff Current	I_{CBO}			100	nA	2SD1006	$V_{CB}=100\text{ V}, I_E=0$
				100	nA	2SD1007	$V_{CB}=120\text{ V}, I_E=0$
Emitter Cutoff Current	I_{EBO}			100	nA	$V_{EB}=5.0\text{ V}, I_C=0$	
DC Current Gain	h_{FE1}	45	200			$V_{CE}=1.0\text{ V}, I_C=5.0\text{ mA}$ ***	
DC Current Gain	h_{FE2}	90	200	400		$V_{CE}=1.0\text{ V}, I_C=100\text{ mA}$ ***	
Collector Saturation Voltage	$V_{CE(sat)}$		0.3	0.6	V	$I_C=500\text{ mA}, I_B=50\text{ mA}$ ***	
Base Saturation Voltage	$V_{BE(sat)}$		0.9	1.5	V	$I_C=500\text{ mA}, I_B=50\text{ mA}$ ***	
Base to Emitter Voltage	V_{BE}	550	620	650	mV	$V_{CE}=10\text{ V}, I_C=10\text{ mA}$ ***	
Gain Bandwidth Product	f_T		90		MHz	$V_{CE}=10\text{ V}, I_E=-10\text{ mA}$	
Output Capacitance	C_{ob}		10		pF	$V_{CB}=10\text{ V}, I_E=0, f=1.0\text{ MHz}$	

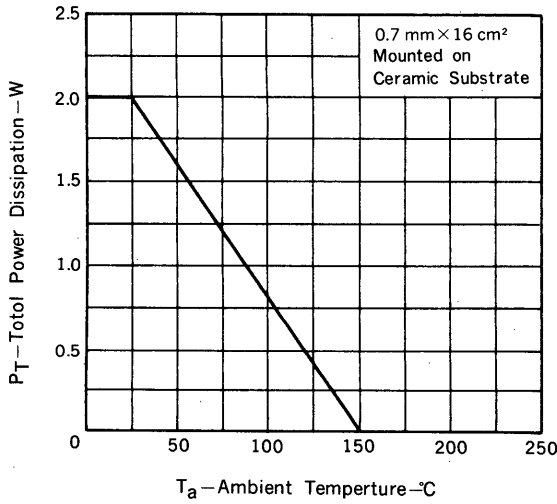
***Pulsed: PW \leq 350 μs , duty cycle \leq 2 %

h_{FE} Classification

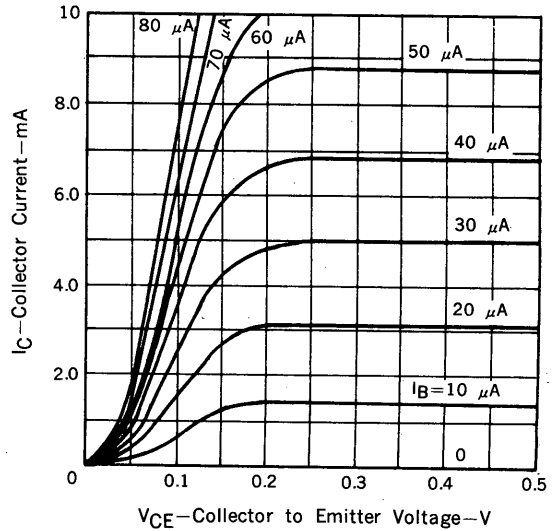
MARKING	2SD1006	HM	HL	HK
		2SD1007	HR	HQ
h_{FE}		90 - 180	135 - 270	200 - 400

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

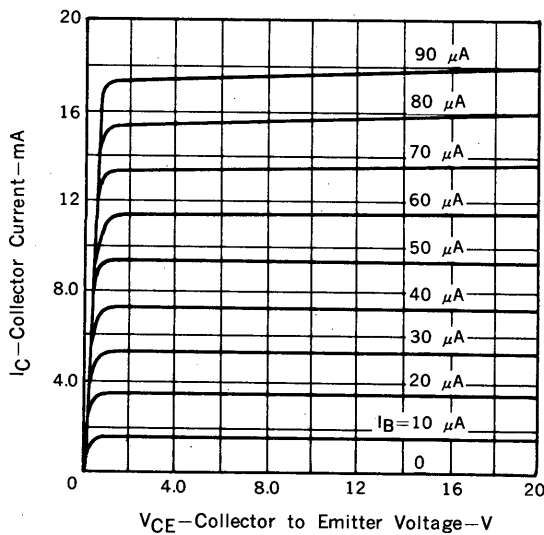
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



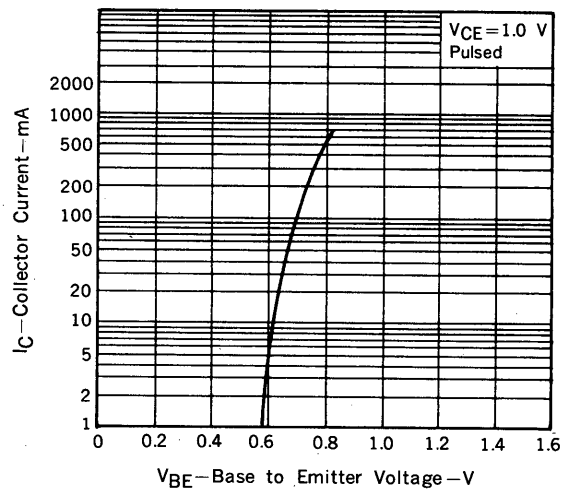
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



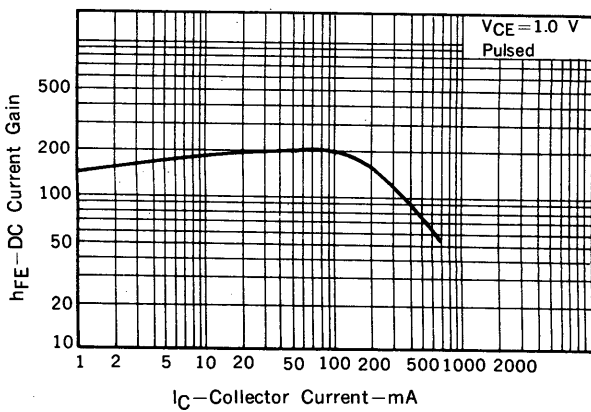
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



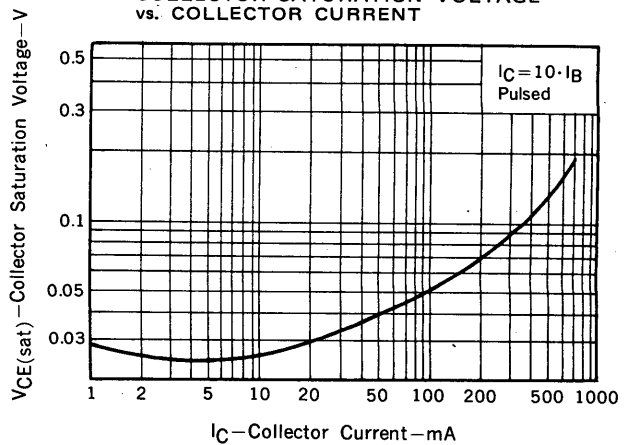
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



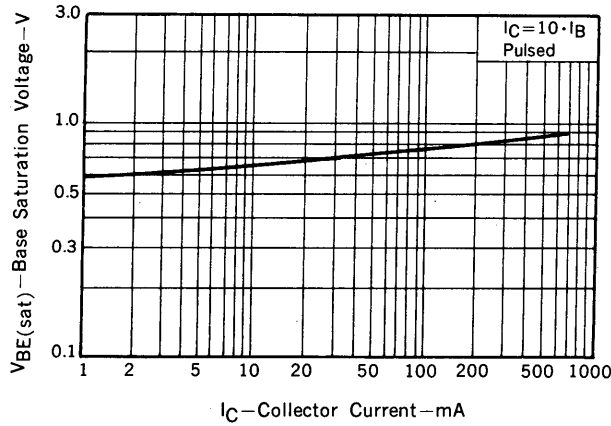
DC CURRENT GAIN vs. COLLECTOR CURRENT



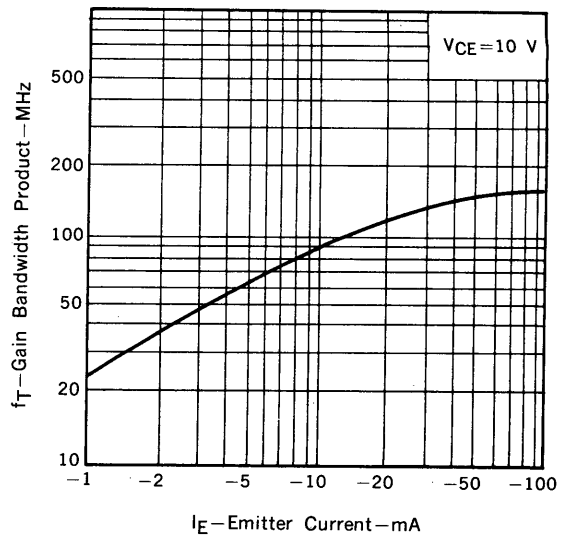
COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



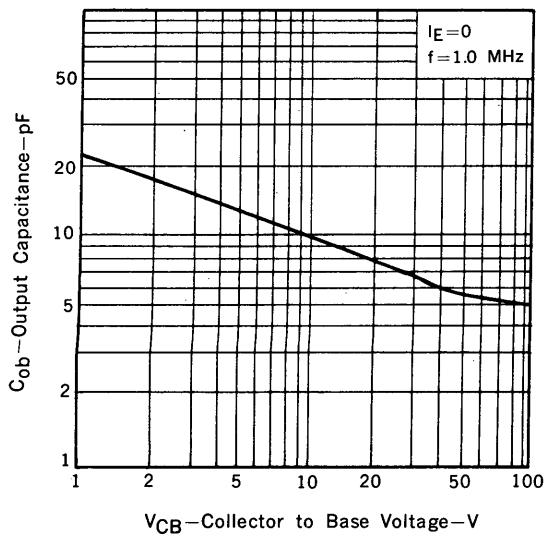
BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



OUTPUT CAPACITANCE vs. REVERSE VOLTAGE



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

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